

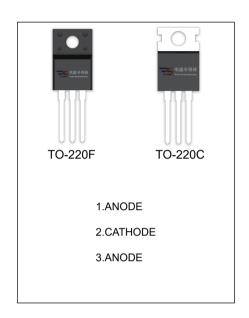
# SBD40150TCTB SBDF40150TCTB SCHOTTKY BARRIER RECTIFIER

### MAIN CHARACTERISTICS

Io	40 (2×20) A
$V_{RRM}$	150 V
T <sub>j</sub>	150 ℃
$V_{F(typ)}$	0.69V (@Tj=125℃)

### **FEATURES**

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



# MAXIMUM RATINGS ( T<sub>a</sub>=25℃ unless otherwise noted )

Cumbal	Parameter	SBD		Heit	
Symbol	Parameter		F40150TCTB	Unit	
V <sub>RRM</sub>	Peak repetitive reverse voltage	150			
V <sub>RWM</sub>	Working peak reverse voltage			V	
$V_R$	DC blocking voltage				
V <sub>R(RMS)</sub>	RMS reverse voltage	105		V	
lo	Average rectified output current	40		Α	
I <sub>FSM</sub>	Non-Repetitive peak forward surge current (8.3ms half sine wave)	250		Α	
R <sub>OJc</sub>	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	°C/W	
R <sub>OJA</sub>	Thermal resistance from junction to ambient	62.5		°C/W	
Tj	Junction temperature	150		℃	
T <sub>stg</sub>	Storage temperature	-55~+150		℃	

## ELECTRICAL CHARACTERISTICS (T₂=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	IR=	0.1mA 150	150			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =150V	Tj =25℃		5	100	uA
			Tj =125℃		5		mA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =10A	Tj =25℃		0.73		V
			Tj =125℃		0.58		V
		I <sub>F</sub> =20A	Tj =25℃		1.01	1.1	V
			Tj =125℃		0.69		V

<sup>\*</sup>Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



